



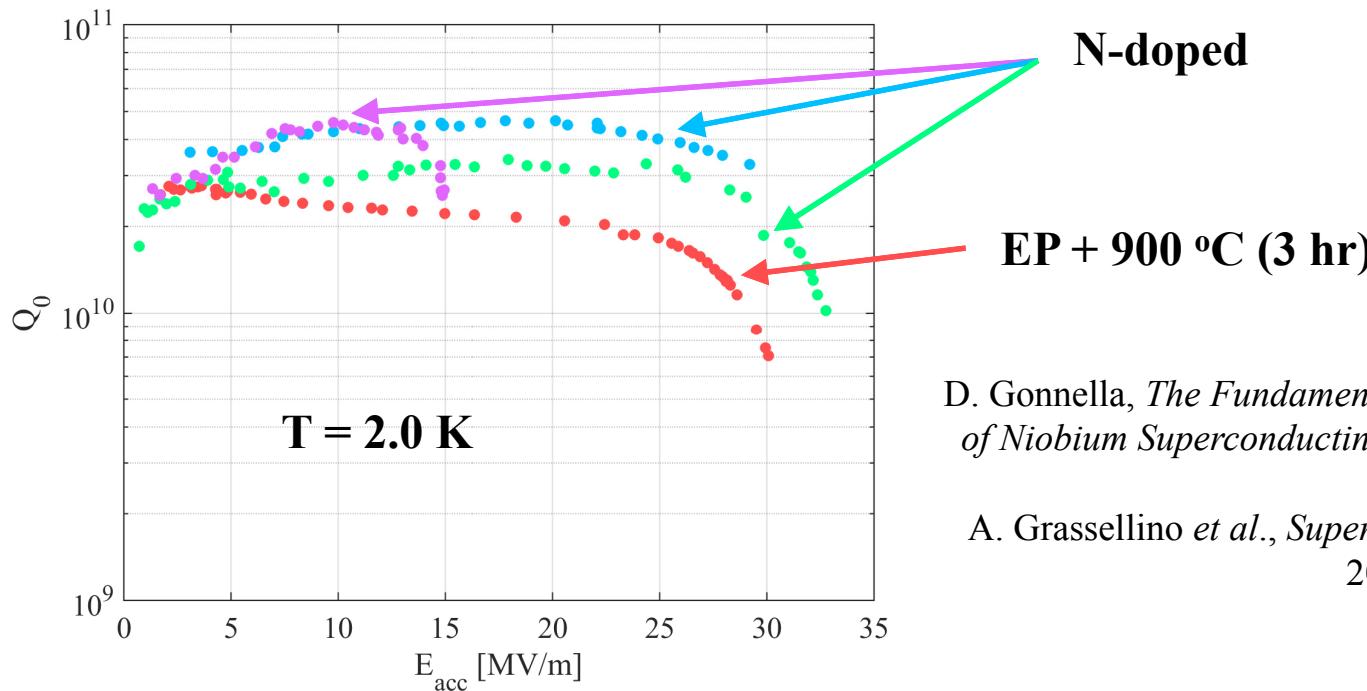
# Low Temperature Doping of Niobium Cavities: What is Really Going on?

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- In high temperature nitrogen doping (**800 – 1000 °C**), nitrides form on cavity surface – nitrogen diffuses from nitride into niobium
- Diffuses **several microns** in **matter of minutes** reducing the electron **mean free path** in the RF layer (see [TUYAA01](#) for explanation)
- Results in **anti- $Q$ -slope** and **higher  $Q_0$**  values



D. Gonnella, *The Fundamental Science of Nitrogen Doping of Niobium Superconducting Cavities*. PhD Thesis. 2016.

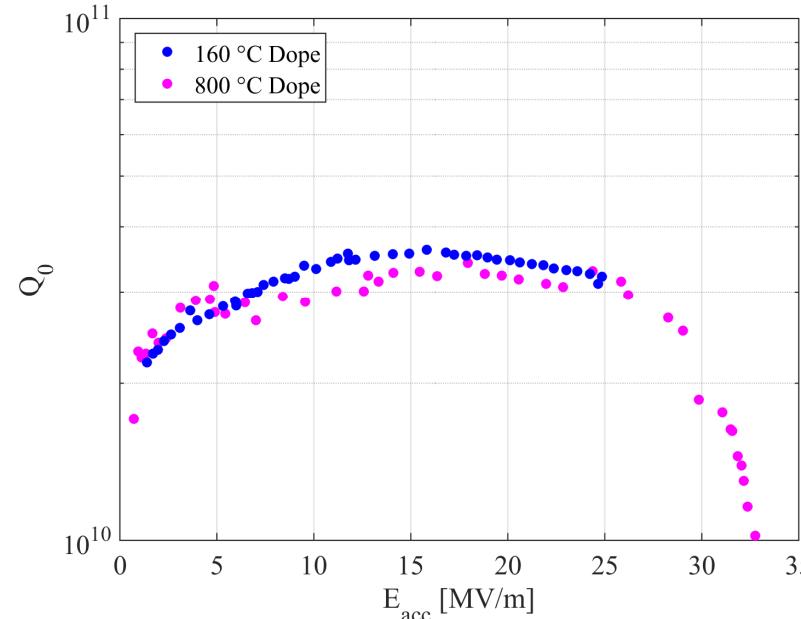
A. Grassellino *et al.*, *Supercond. Sci. Tech.*, **26**(102001), 2013.



- Low temperature baking (**120 – 160 °C**) in a low pressure **nitrogen** atmosphere results in ‘***Q*-rise**’ and **higher low-field *Q*<sub>0</sub> values**

A. Grassellino *et al.*, *Unprecedented Quality Factors at Accelerating Gradients up to 45 MV/m in Niobium Superconducting Resonators via Low Temperature Nitrogen Infusion*. [arXiv:1701.06077](https://arxiv.org/abs/1701.06077).

P. N. Koufalis, D. L. Hall, M. Liepe, J. T. Maniscalco. *Effects of Interstitial Oxygen and Carbon on Niobium Superconducting Cavities*. [arXiv:1612.08291](https://arxiv.org/abs/1612.08291).



- Nitrogen diffuses **only 2 – 5 nm** into niobium at these temperatures
- Observed that **carbon** and **oxygen diffuse significantly** into niobium at **160 °C**



1. Is **nitrogen** in the first **~2–5 nm** of the surface affecting cavity performance?
2. Could **carbon** and **oxygen** be responsible for the observed  **$Q$ -rise** and **high  $Q_0$** ?
3. How do **carbon**, **nitrogen**, and **oxygen** interact with each other in the lattice?
4. Can **other gases** be used for **low temperature doping**?
5. What are sources of **carbon**, **nitrogen**, and **oxygen**?

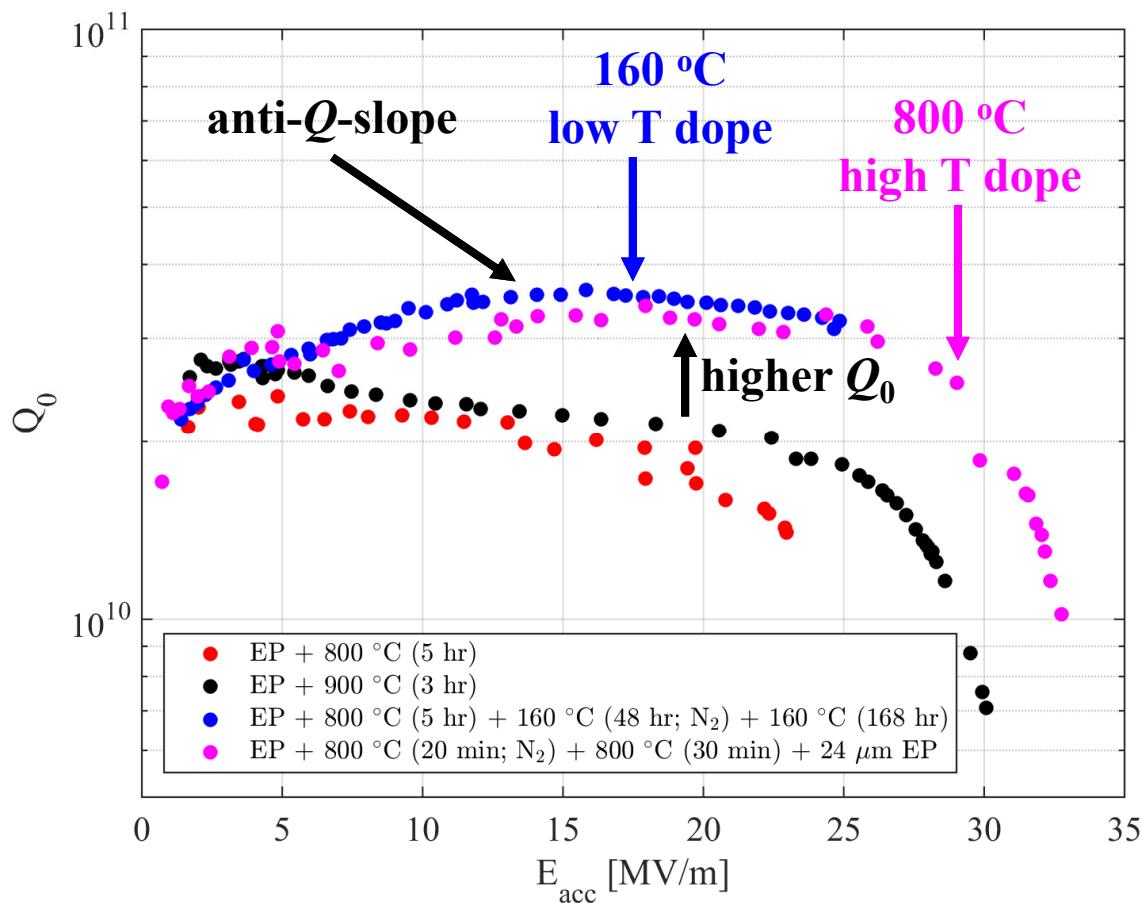
*What is going on?*



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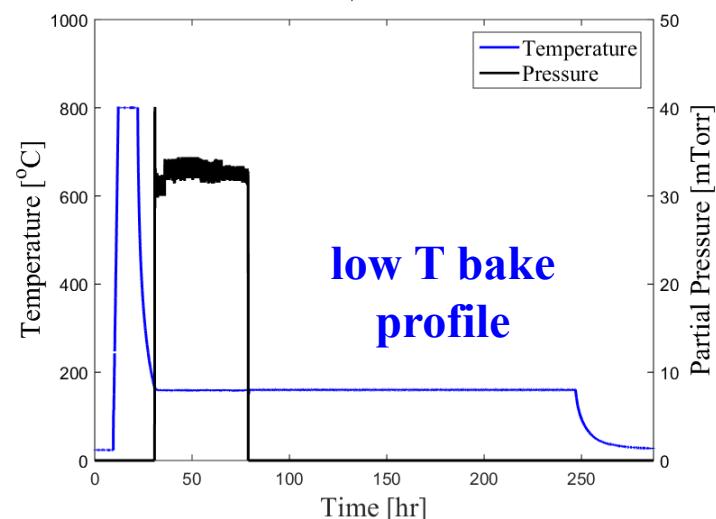


# RF Performance



Max Quality Factor:  
 $Q_0 = 3.6 \times 10^{10} @ 16 \text{ MV/m}$

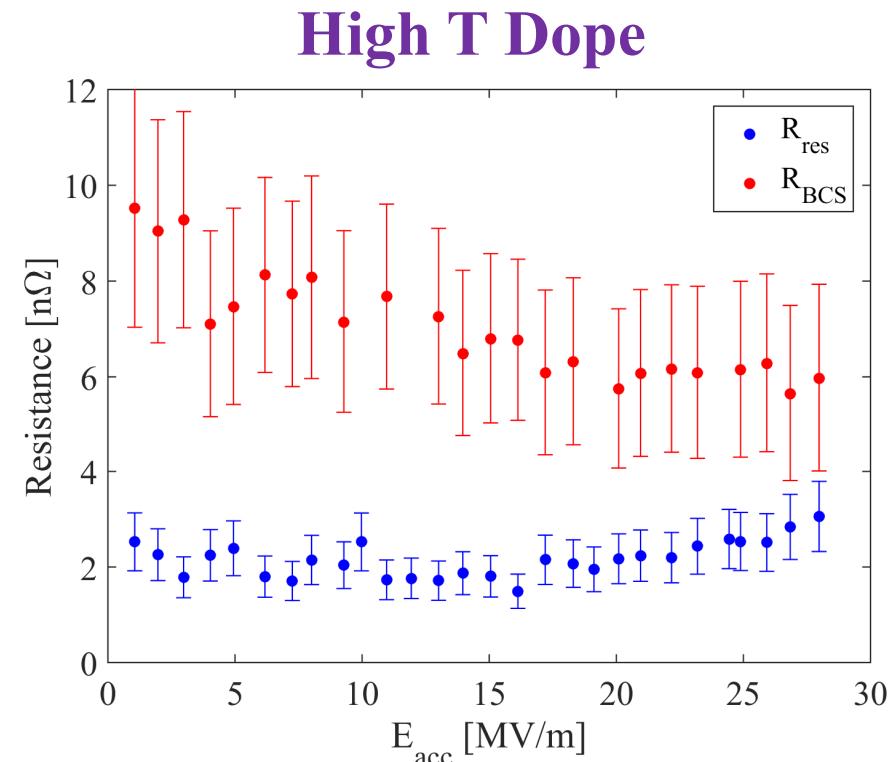
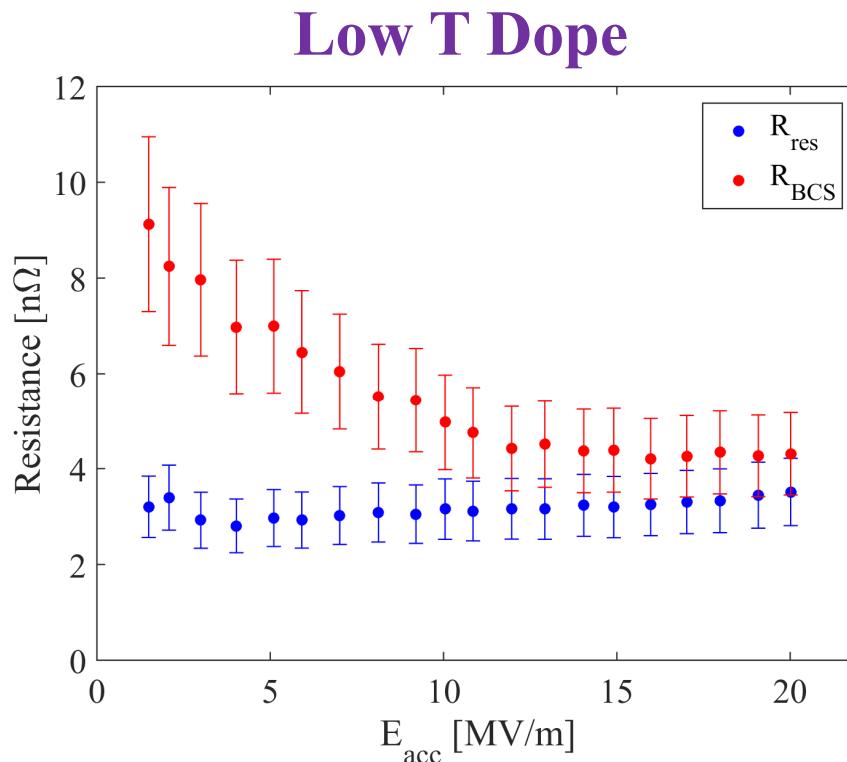
Continuously flowing  
N<sub>2</sub> atmosphere!



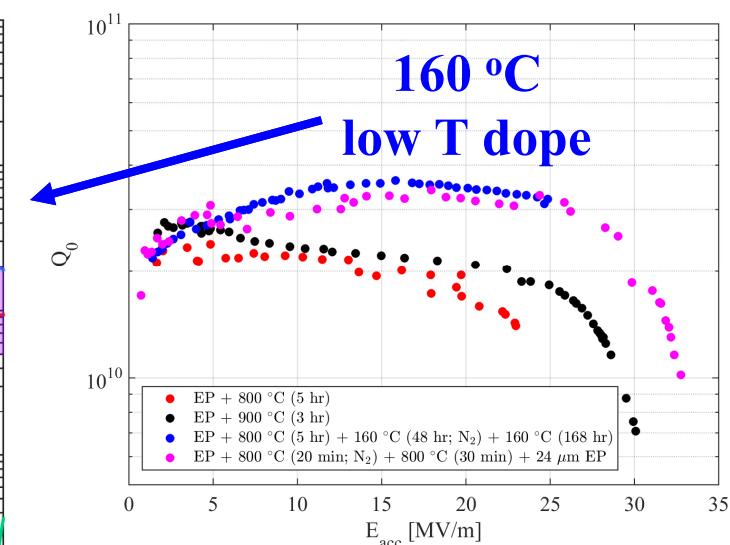
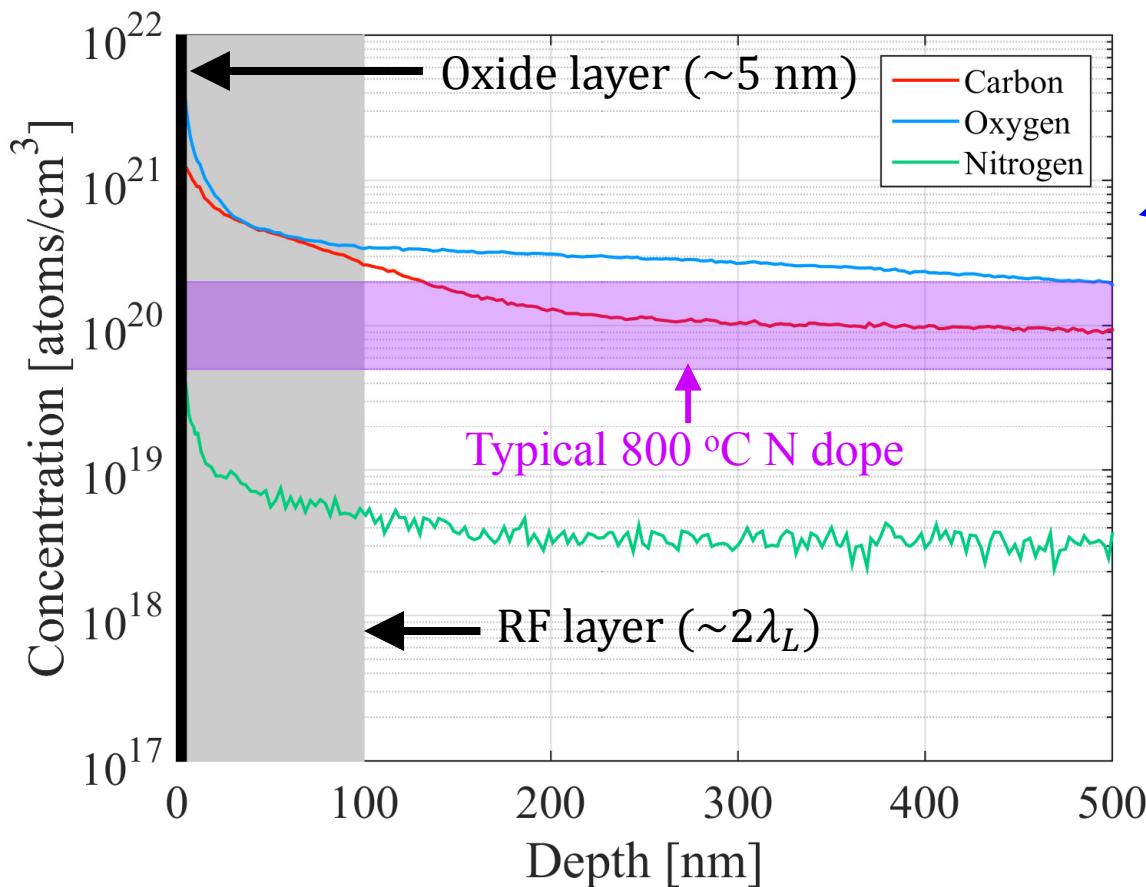
Thermal Quench:  
**25 MV/m ( $B_{\text{pk}} \sim 107 \text{ mT}$ )**



- $R_{BCS}$  decreases with increasing  $E_{acc}$ ; same effect seen in high- $T$  nitrogen-doped cavities (caused by reduction of mean free path!)



- Which impurity is reducing the mean free path?



**Carbon** and **oxygen** concentrations two orders of magnitude higher than **nitrogen** in RF layer

Typical concentration between  $\sim 5 \times 10^{19} - 2 \times 10^{20}$  cm<sup>-3</sup> or (0.09 – 0.36 at. % N) for N-doped cavities



# Estimated Mean Free Path

- Concentration at **depth of 50 nm** used to calculate **estimate for mean free path**

$$l = \frac{\sigma}{a \cdot c}$$

$$\sigma = 0.37 \times 10^{-15} \Omega \cdot m^2 ; a = \begin{cases} 4.3 \times 10^{-8} \Omega \cdot m (C, O) \\ 5.2 \times 10^{-8} \Omega \cdot m (N) \end{cases} ; c = \text{impurity concentration}$$

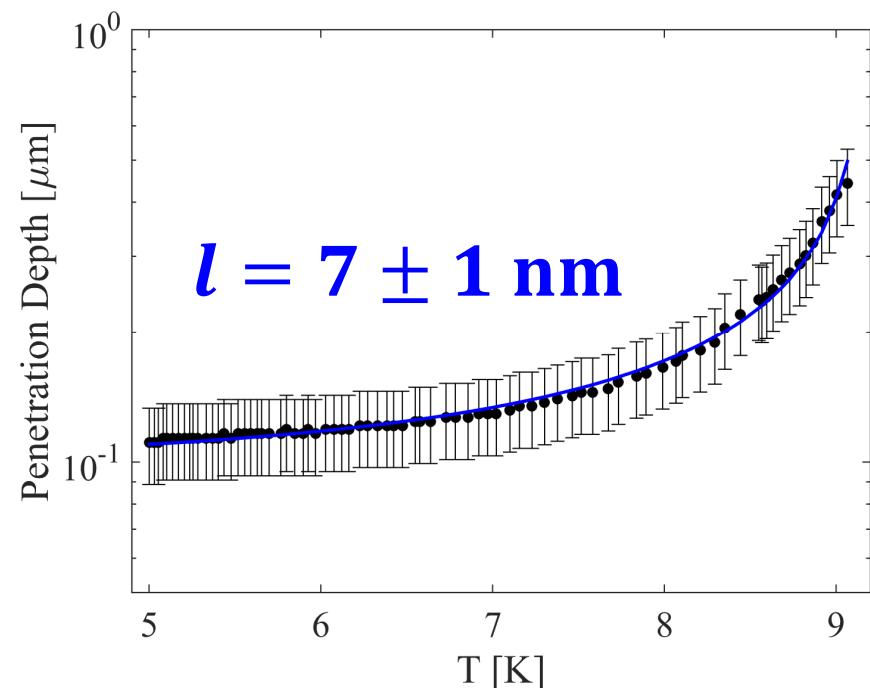
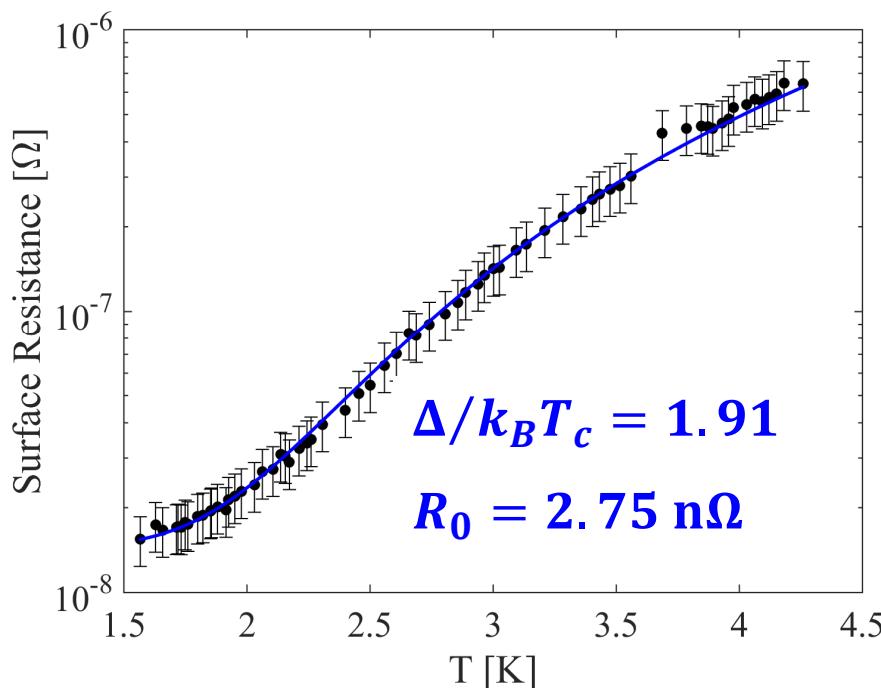
MFP @ depth = 50 nm	
C + O	5 nm
N	712 nm

- Prediction of **mean free path** is **5 nm** based on the SIMS data – very short!



- RF measurements of  $\Delta\lambda$  vs.  $T$  and  $R_S$  vs.  $T$  with BCS fit of **mean free path, energy gap, and residual resistance**
- Measured and estimated  $l$  in good agreement!

## Low T Dope





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# Sample Analysis



# Sample Studies

- Secondary ion mass spectroscopy (SIMS) was used to analyze single-crystal niobium samples prepared at various baking temperatures and durations to determine the impurity content in the first 500 nm
- All samples underwent a ~150 um EP before being de-gassed at 800 °C high vacuum for 5 hr; low  $T$  treatment began immediately after de-gas!
- Samples were wrapped in niobium foil to prevent furnace contamination
- Recipes you will see throughout presentation shown in table

Sample #	Baking Recipe
1	800 °C (5 hr)
2	800 °C (5 hr) + 160 °C (48 hr)
3	800 °C (5 hr) + 160 °C (48 hr; N <sub>2</sub> )
4	800 °C (5 hr) + 160 °C (96 hr; N <sub>2</sub> )
5	800 °C (5 hr) + 120 °C (48 hr; N <sub>2</sub> )
6	800 °C (5 hr) + 160 °C (48 hr; Ar) – 99.999 %
7	800 °C (5 hr) + 160 °C (48 hr; Ar) – 99.9999 %
8	800 °C (5 hr) + 160 °C (48 hr; Ar + CO <sub>2</sub> ) – 10 ppm CO <sub>2</sub>

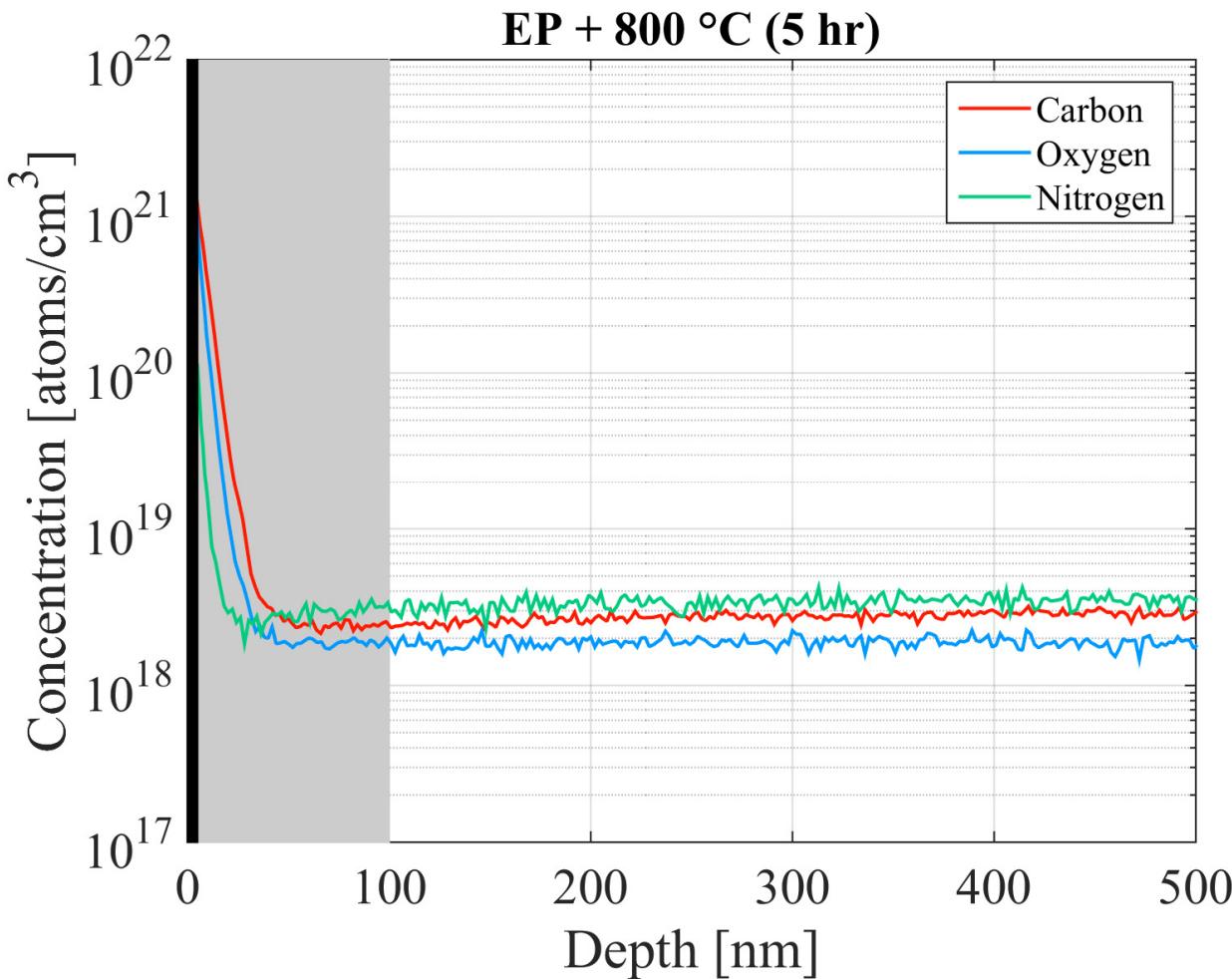




- How does bake **temperature** and **duration** affect **concentration profiles** of **C**, **N**, and **O**?
- Can **other gases** be used for **low temperature doping**?
- Sources of **C**, **N**, and **O**?

Sample #	Baking Recipe
1	800 °C (5 hr)
2	800 °C (5 hr) + 160 °C (48 hr)
3	800 °C (5 hr) + 160 °C (48 hr; N <sub>2</sub> )
4	800 °C (5 hr) + 160 °C (96 hr; N <sub>2</sub> )
5	800 °C (5 hr) + 120 °C (48 hr; N <sub>2</sub> )
6	800 °C (5 hr) + 160 °C (48 hr; Ar) – <b>99.999 %</b>
7	800 °C (5 hr) + 160 °C (48 hr; Ar) – <b>99.9999 %</b>
8	800 °C (5 hr) + 160 °C (48 hr; Ar + CO <sub>2</sub> ) – 10 ppm CO <sub>2</sub>





Degassing **800 °C** vacuum  
**bake** for 5 hr

**C, N, and O** concentrations  
**drop off rapidly** to  
background levels

**High mobility** of all three  
impurities **at this temperature**

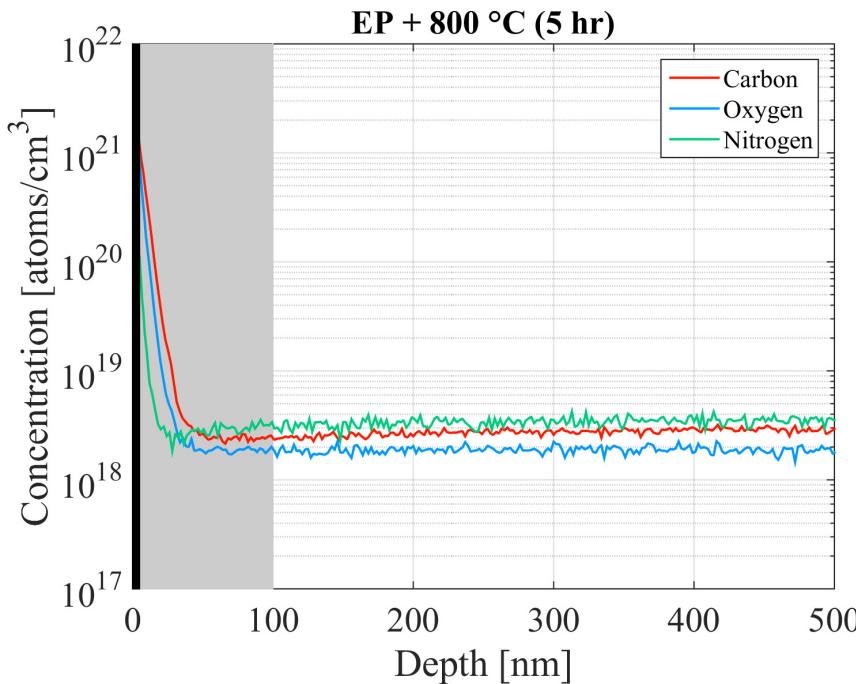
Background level  $\sim 1 \times 10^{18} - 5 \times 10^{18}$  cm<sup>-3</sup>



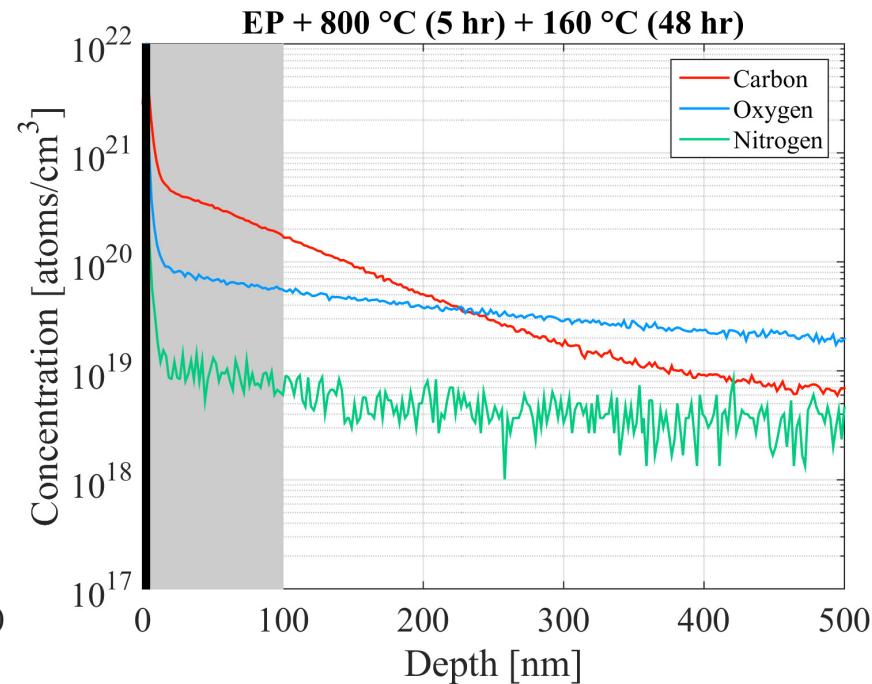
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# Nitrogen Baking

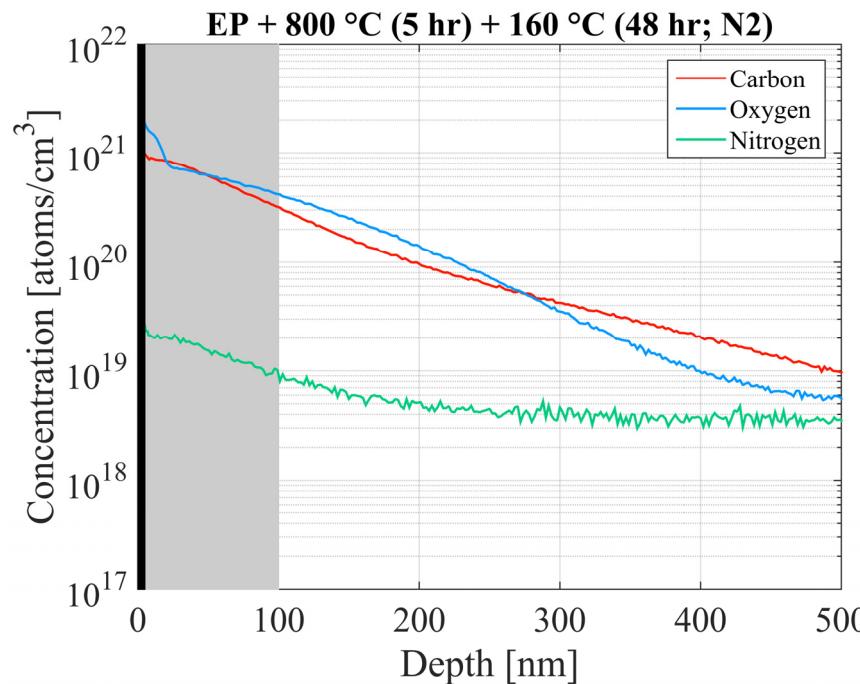


**Baseline**

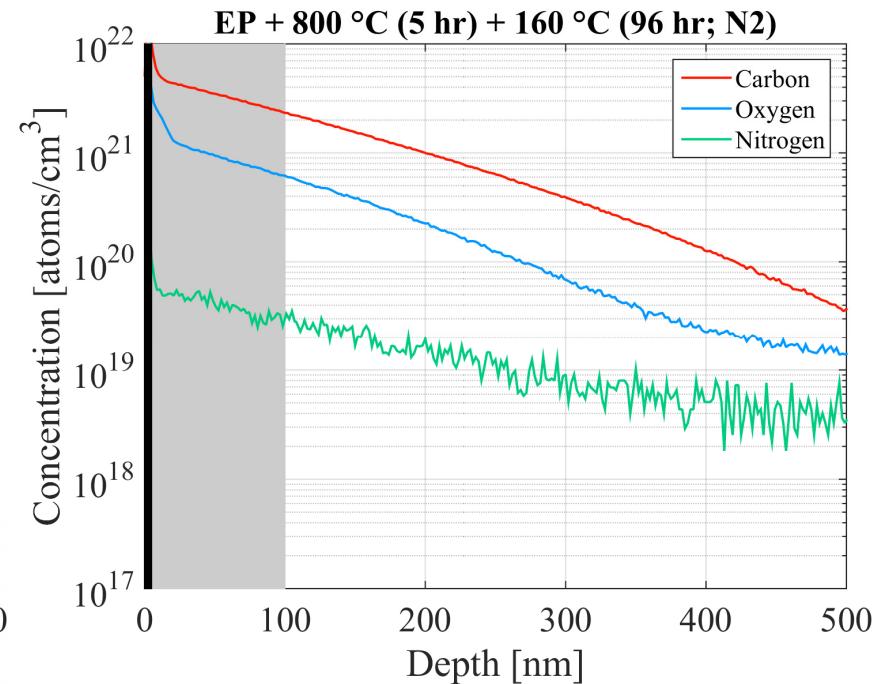


**+ 48 hr @ 160 °C**

Niobium acts as a very **good getter in vacuum** – absorbs residual gases in furnace such as H<sub>2</sub>O, O<sub>2</sub>, CO, CO<sub>2</sub>, N<sub>2</sub>, etc.



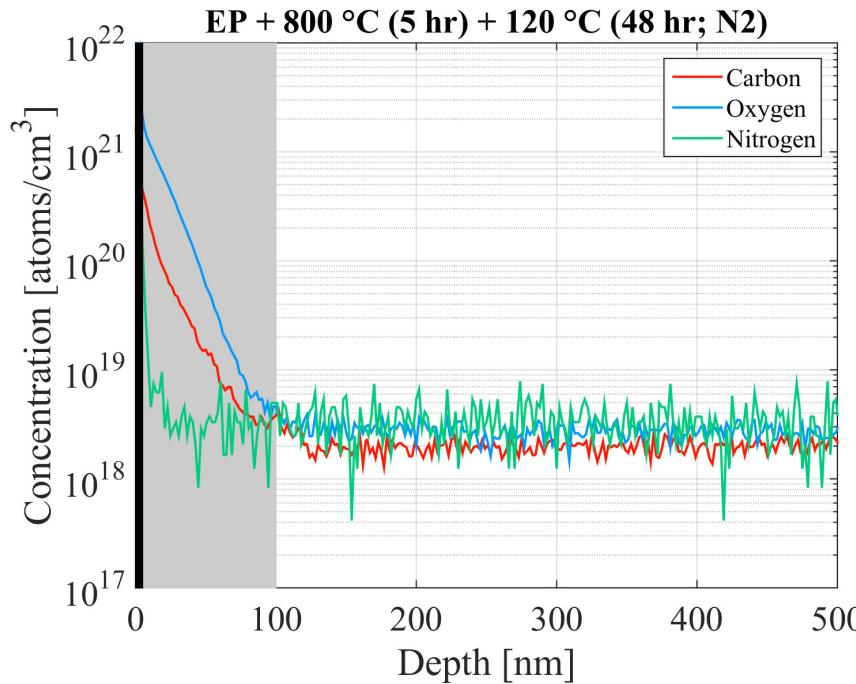
**48 hr @ 160 °C**



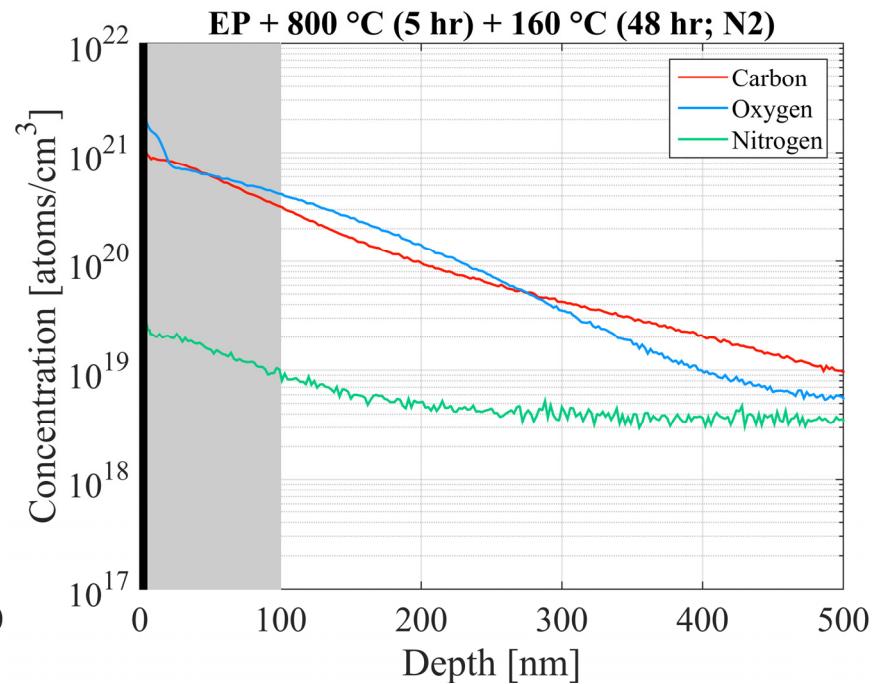
**96 hr @ 160 °C**

The diffusion length increases for carbon, nitrogen, and oxygen as when doping time is increased.

$$L_{\text{diff}} = \sqrt{Dt}$$



120 °C



160 °C

The diffusion length increases for carbon, nitrogen, and oxygen as when doping temperature increases.

$$L_{\text{diff}} = \sqrt{Dt}$$

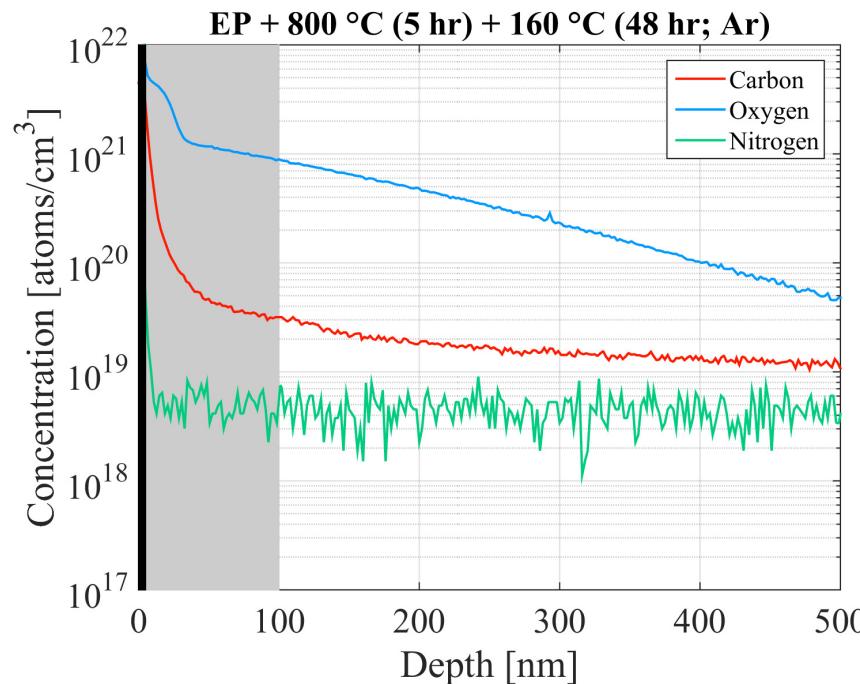
$$D = D(T)$$



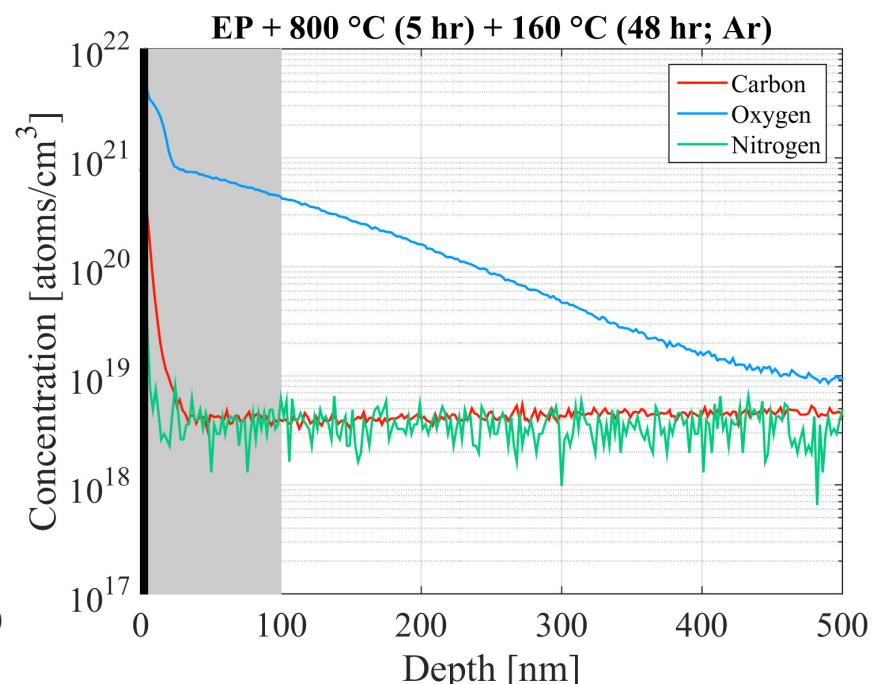
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# Argon Baking

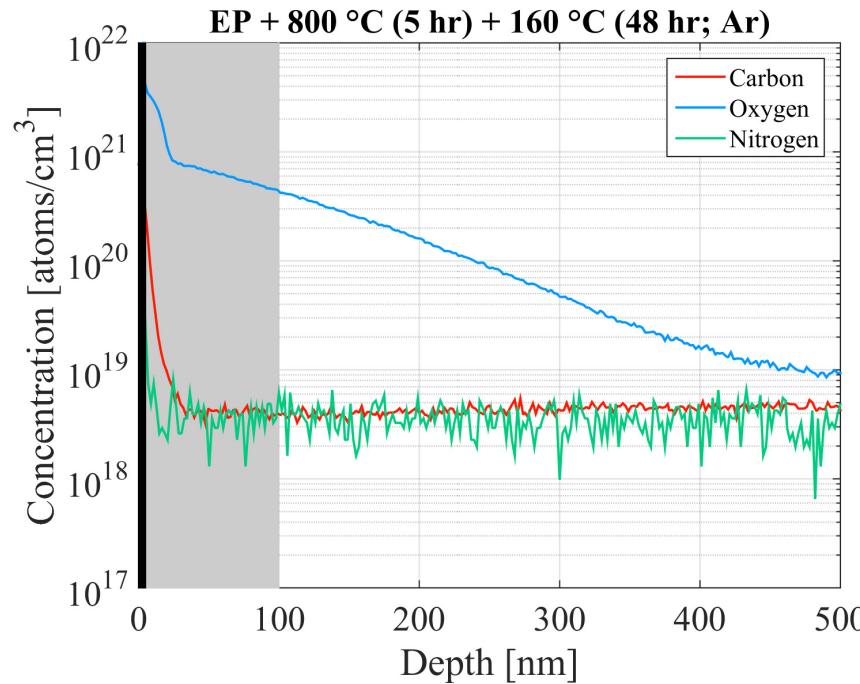


Ultra High Purity Argon  
**(99.999 %)**

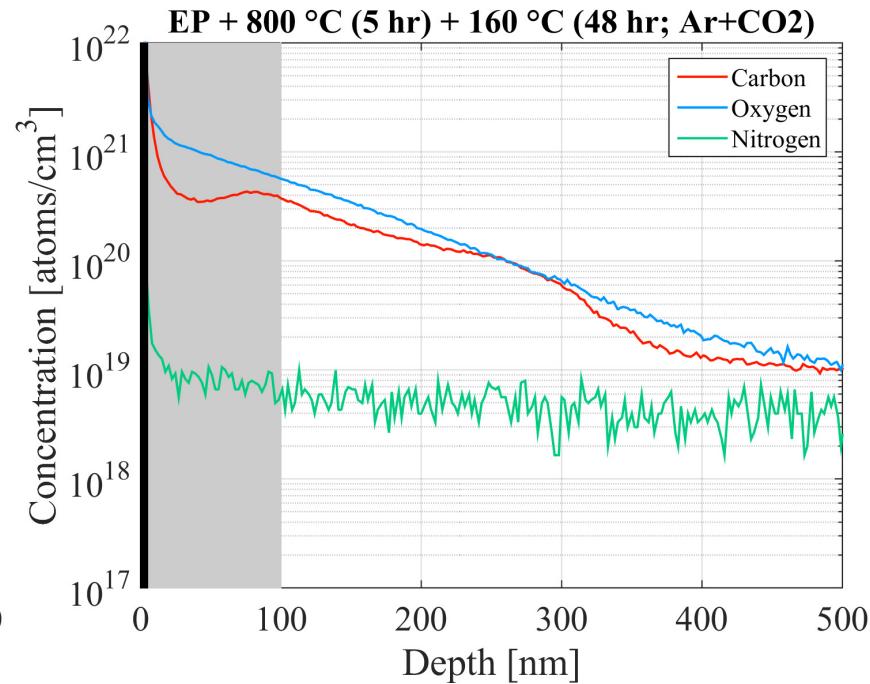


Research Plus Argon  
**(99.9999 %)**

The **purity of gas** used has a **high impact** on the **impurity concentration!** The argon with higher trace impurities leads to a higher concentration in the RF layer.

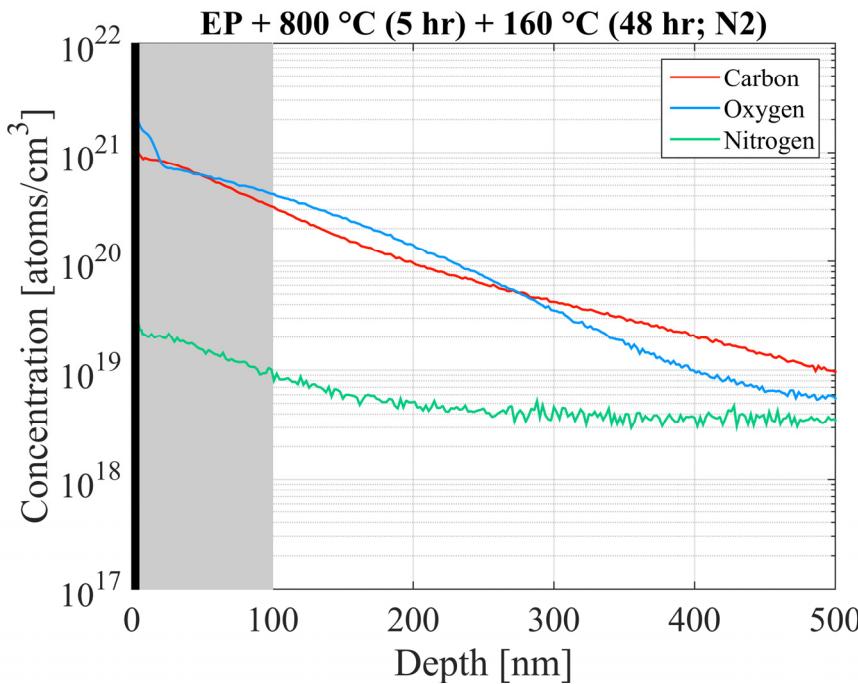


Research Plus Argon  
**(99.9999 %)**

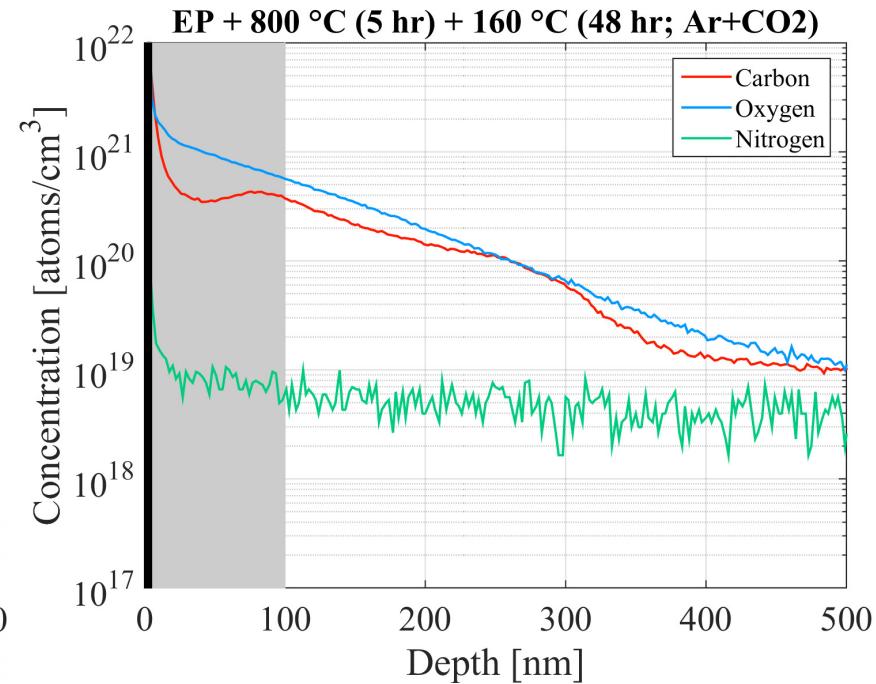


Research Plus Argon + 10 ppm CO<sub>2</sub>  
**(99.9999 %)**

The research plus argon mixed with 10 ppm CO<sub>2</sub> significantly increases the concentration of carbon in the niobium! Trace impurities in the gas are important.



Nitrogen



RP Argon + 10 ppm CO<sub>2</sub>

Argon gas mixture can be used to test whether or not nitrogen has an impact on performance.



# Concluding Remarks

- **Anti- $Q$ -slope** is correlated with **shorter mean free path** ( $l < 100$  nm)
  - Shorter mean free path → stronger anti- $Q$ -slope

J. T. Maniscalco, D. Gonnella, M. Liepe. *J. App. Phys.* **121**, 043910 (2017).

## TUYAA01

- For low temperature baking (**120 – 160 °C**), **C** and **O** dominate in the reduction of the mean free path resulting in same effects observed in high temperature doping:
  - **anti- $Q$ -slope** and **increased low-field  $Q_0$**  values
- Future work:
  - Cavity testing with various recipes used for sample baking
  - Further sample analysis
  - Sensitivity to trapped magnetic flux
  - Interactions between impurities?